



修订记录 / Revised record

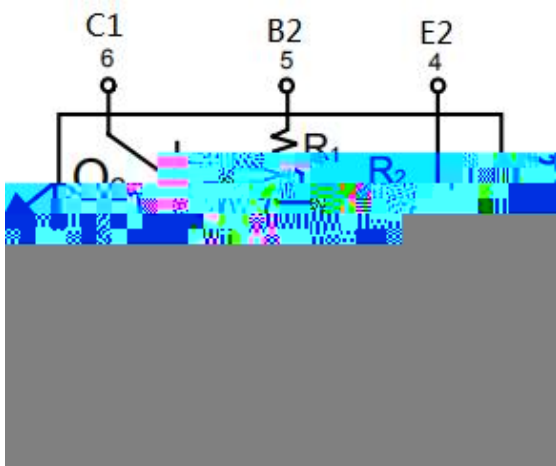
A	2020.08.21		LRC-LMUN5314DW1T1G		
B	2021-11-25	6			

SOT-363 NPN+PNP

Double silicon NPN and PNP transistor in a SOT-363 Plastic Package

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, Halogen-free Product.

Switching applications, interface circuit and driver circuit applications.

**放大及印章代码 / h_{FE} Classifications & Marking**

Marking

H314



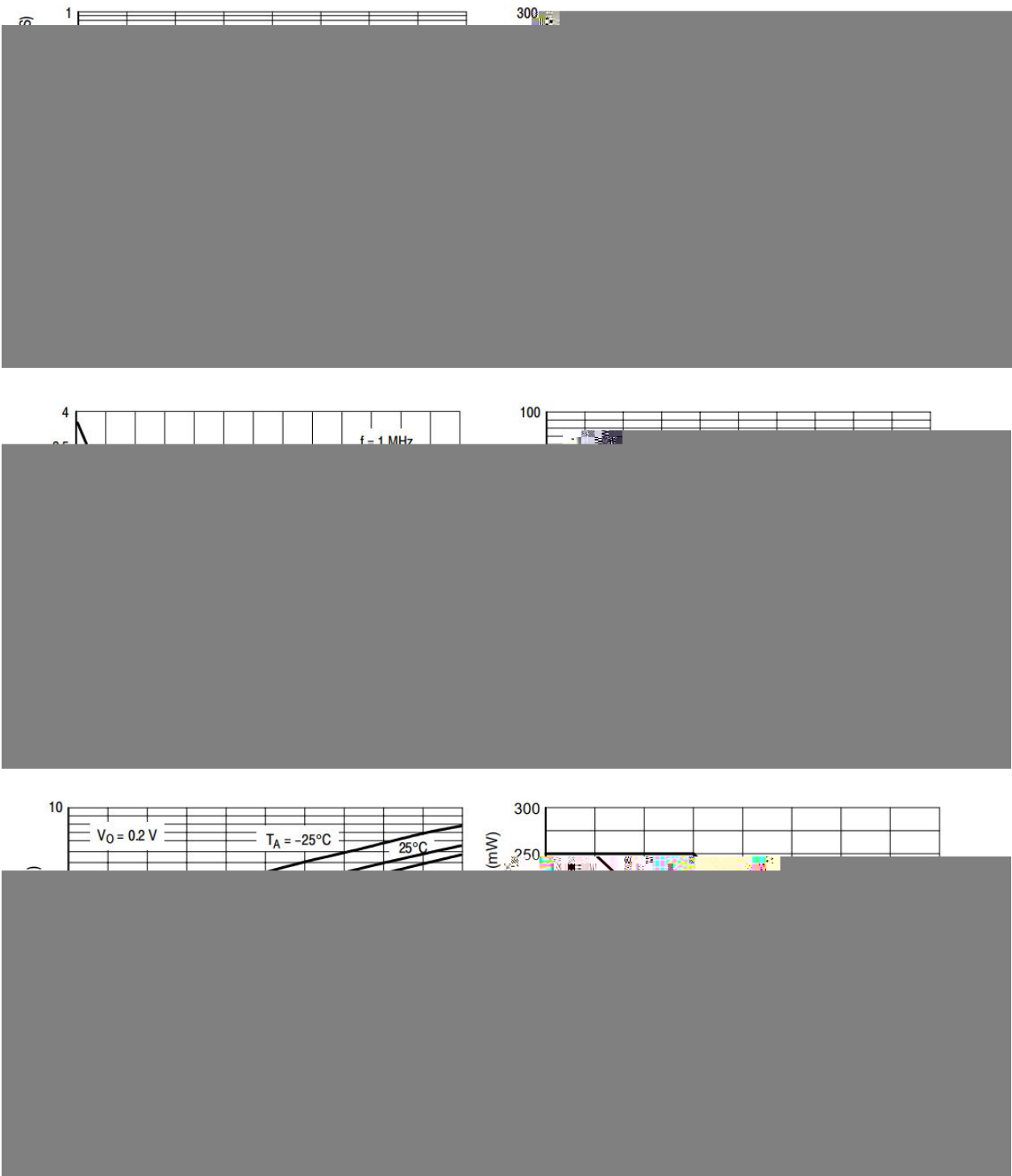
Parameter	Symbol	Rating	Unit
Output Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	40	V
		-6	V
Output Current	I_C	100	mA
	I_O	70	mA
Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage(OFF)	$V_{I(off)}$	$V_{CC}=5.0V$ $I_O=100\mu A$			0.3	V
Input Voltage(ON)	$V_{I(on)}$	$V_O=0.3V$ $I_O=1mA$	1.4			V
Output Voltage	$V_{O(on)}$	$I_O=5mA$ $I_I=0.25mA$		0.1	0.3	V

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电参数曲线图 / Electrical Characteristic Curve(NPN)



BRMUN5314WS

Rev.B Nov.-2021

BRMUN5314WS

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印章说明 / Marking Instructions

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Note:



“1” Pin

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Product Type Code

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Lot No. Code, code change with Lot No.

